

### General Description

The WSD4070DN is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD4070DN meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

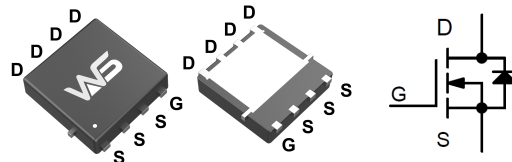
### Product Summary

BVDSS	RDSON	ID
40V	4.5mΩ	68A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### DFN3.3X3.3-EP Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^G$	68	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^G$	35	A
$I_{DM}@T_C=25^\circ C$	Pulsed Drain Current <sup>C</sup>	144	A
EAS	Avalanche Energy, Single Pulse (L=0.3mH)	80	mJ
$I_{AS}$	Avalanche Current	40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>A</sup>	3.1	W
$P_D@T_A=70^\circ C$	Total Power Dissipation <sup>A</sup>	2.0	W
$T_J$ $T_{STG}$	Storage and Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>A</sup>	---	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>A</sup>	---	2.8	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A	---	4.5	5.5	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	5.3	7.6	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.4	1.9	2.4	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-6.	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	-	2	uA
		V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	-	10	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	-	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	---	67	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	0.8	1.5	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	---	28	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.9	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	6.0	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =20V, R <sub>L</sub> =1Ω, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω.	---	7.2	---	ns
T <sub>r</sub>	Rise Time		---	3.0	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	23	---	
T <sub>f</sub>	Fall Time		---	3.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	---	2420	---	pF
C <sub>oss</sub>	Output Capacitance		---	220	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	150	---	

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> t ≤ 10s value and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C.

## Typical Operating Characteristics

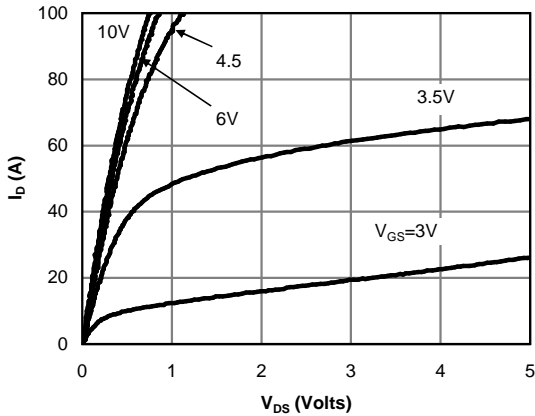


Fig 1: On-Region Characteristics (Note E)

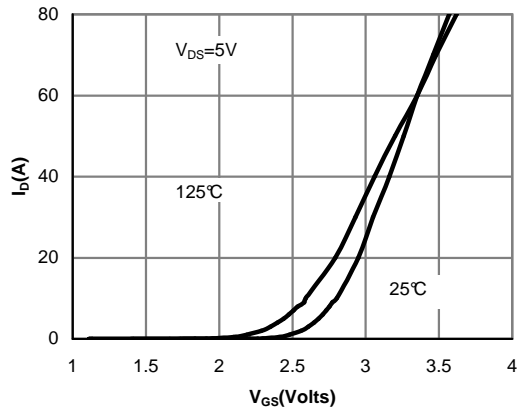


Figure 2: Transfer Characteristics (Note E)

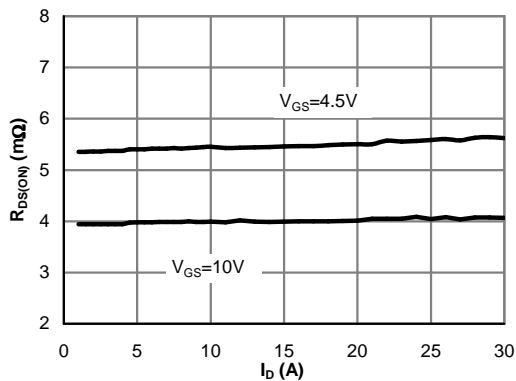


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

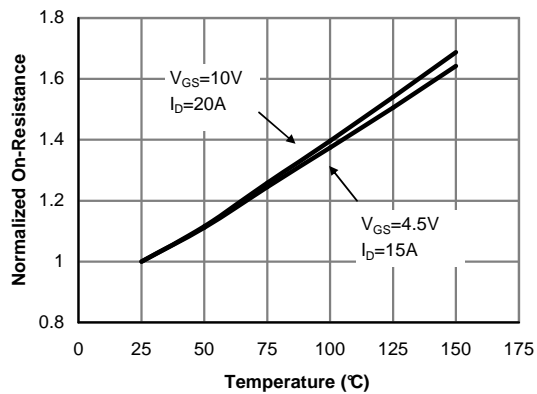


Figure 4: On-Resistance vs. Junction Temperature (Note E)

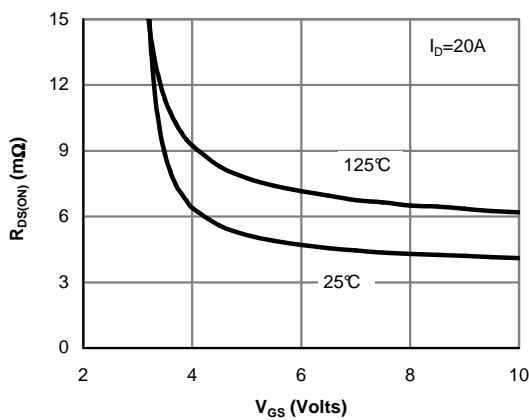


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

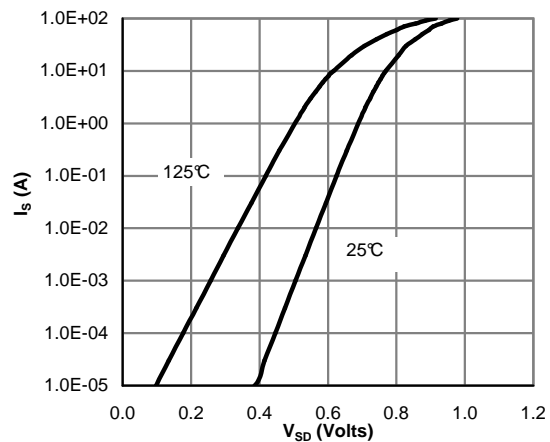


Figure 6: Body-Diode Characteristics (Note E)

**Typical Operating Characteristics (Cont.)**

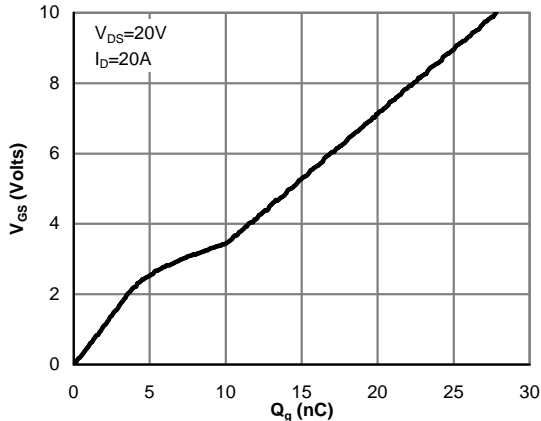


Figure 7: Gate-Charge Characteristics

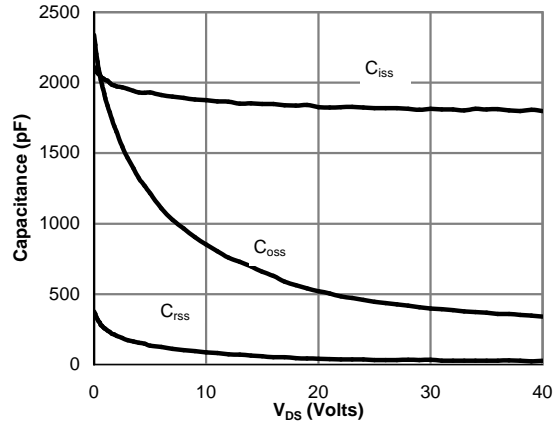


Figure 8: Capacitance Characteristics

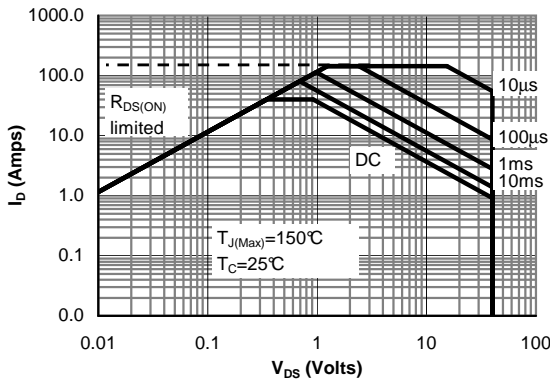


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

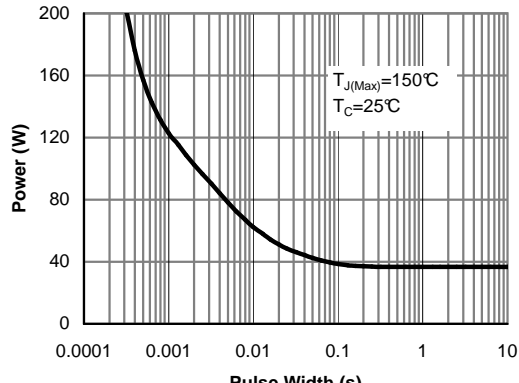


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

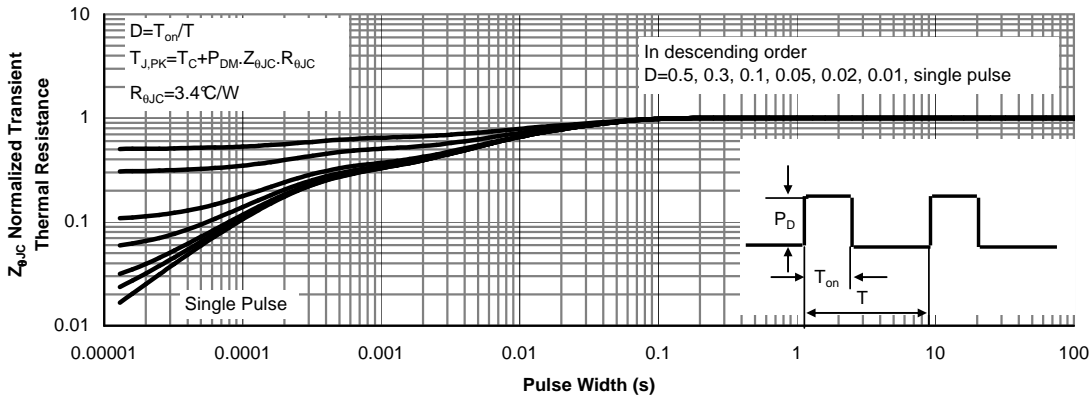


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

**Typical Operating Characteristics (Cont.)**

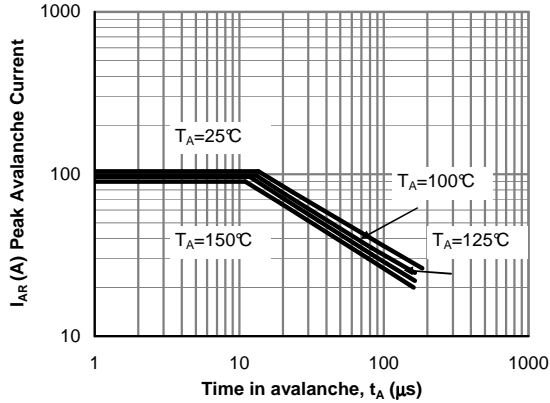


Figure 12: Single Pulse Avalanche capability (Note C)

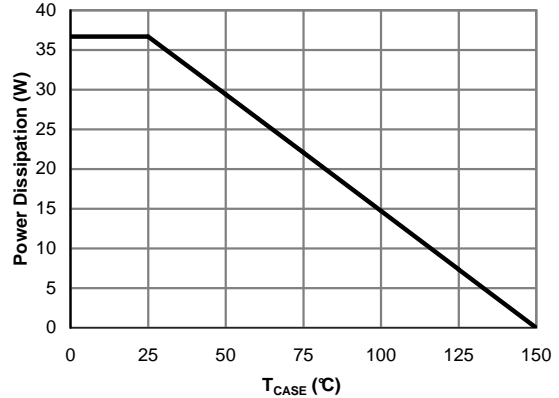


Figure 13: Power De-rating (Note F)

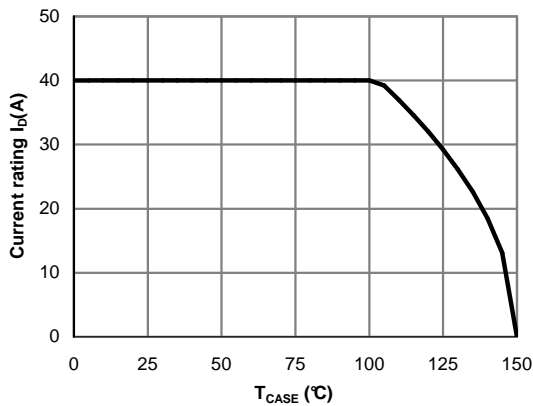


Figure 14: Current De-rating (Note F)

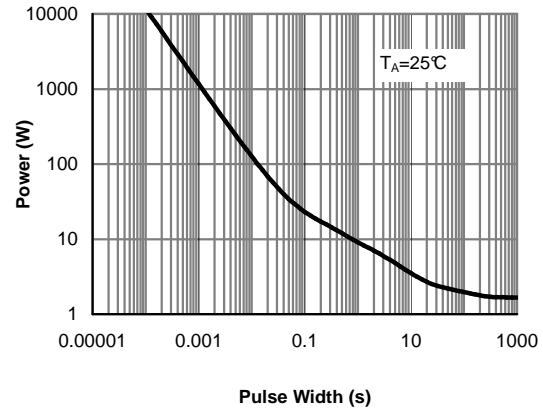


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

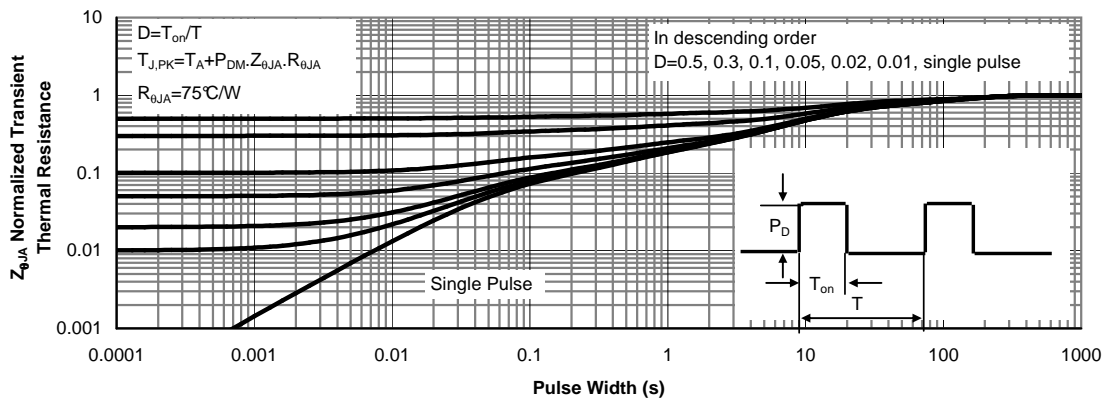


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

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